

A B S T R A C T

A wiring structure of a semiconductor device according to the present invention comprises a first conducting layer for electrically connecting with a semiconductor element or a wiring element formed on a semiconductor substrate, a barrier metal formed on the first conducting layer, and a second conducting layer formed on the barrier metal, for electrically connecting with the first conducting layer via the barrier metal, in which the barrier metal is formed of WN_x (tungsten nitride) or WSi_xNy (tungsten silicide nitride).

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